Abstracts

A C-Band 10 Watt GaAs Power FET

J. Fukaya, M. Ishii, M. Matsumoto and Y. Hirano. "A C-Band 10 Watt GaAs Power FET." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 439-440.

A new GaAs high power FET has been developed. The FET chip with 10.8mm gate-width employs a deep recess, via hole PHS, anair bridge gate-source cross-over and novel gate feeder network technology. The internally matched device which consists of two chips (total gate-width; 21.6mm) has realized 10 watts of 1dB gain compression power with 8dB gain and 43% power added efficiency at 8GHz.

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